



FZT694B

120V NPN MEDIUM POWER HIGH GAIN TRANSISTOR IN SOT223

Features

- BV_{CEO} > 120V
- BV_{CBO} > 120V
- I_C = 1A Continuous Current
- hFE > 400 for High Gain @ 0.2A
- Very Low Saturation Voltage
- Complementary PNP Type: FZT795A
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020 Terminals: Finish - Matte Tin Plated Leads.
- Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

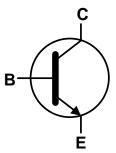
Applications

- Darlington Replacement
- Relay and Solenoid Driver

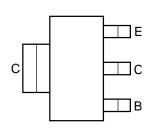




Top View



Device Symbol



Top View Pin-Out

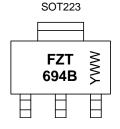
Ordering Information (Notes 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT694BTA	AEC-Q101	FZT694B	7	12	1.000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



FZT 694B = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	$V_{\sf CEO}$	120	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	Ic	1	Α
Peak Pulse Current	I _{CM}	2	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.0		
Power Dissipation	(Note 6)		2.0	W	
Power Dissipation	(Note 7)	P_{D}	1.6	VV	
	(Note 8)		1.2		
	(Note 5)		41.7		
Thermal Desigtance, lungtion to Ambient	(Note 6)		62.5		
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{ heta JA}$	78.1	°C/W	
	(Note 8)		104		
Thermal Resistance Junction to Lead (Note 9)		$R_{ hetaJL}$	12.9		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 10)

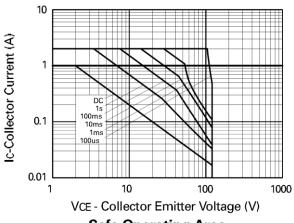
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

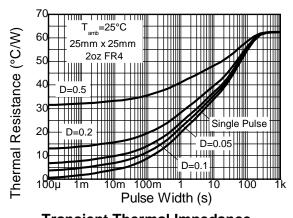
- 5. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 6, except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.
- 8. Same as Note 6, except the device is mounted on minimum recommended pad layout.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



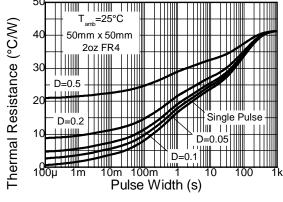
Thermal Characteristics and Derating Information



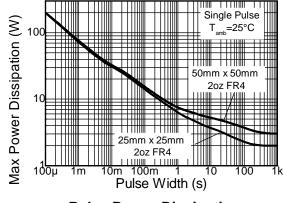
Safe Operating Area



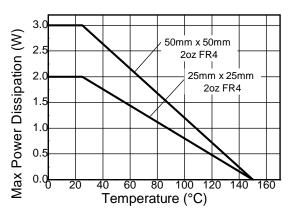
Transient Thermal Impedance



Transient Thermal Impedance



Pulse Power Dissipation



Derating Curve



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

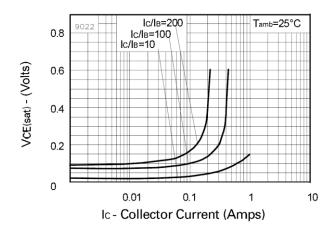
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	120	_	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	120	_	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	_	_	V	I _E = 100μA
Collector-Base Cutoff Current	I _{CBO}	_	_	100	nA	V _{CB} = 100V
Collector-Emitter Cutoff Current	I _{CES}	1	_	100	nA	V _{CE} = 100V
Emitter Cutoff Current	I _{EBO}	_	_	100	nA	V _{EB} = 6V
DC Current Gain (Note 11)	h _{FE}	500 400 150	_ _ _	_ _ _	_	$I_C = 100$ mA, $V_{CE} = 2V$ $I_C = 200$ mA, $V_{CE} = 2V$ $I_C = 400$ mA, $V_{CE} = 2V$
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}	-	_	250 500	mV	$I_C = 100$ mA, $I_B = 0.5$ mA $I_C = 400$ mA, $I_B = 5$ mA
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	_	_	0.9	V	I _C = 1A, I _B = 10mA
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	_	_	0.9	V	I _C = 1A, V _{CE} = 2V
Input Capacitance	C _{ibo}	_	200	_	pF	V _{EB} = 0.5V, f = 1MHz
Output Capacitance	C _{obo}	_	9	_	pF	V _{CB} = 10V, f = 1MHz
Current Gain-Bandwidth Product	f⊤	130	_	_	MHz	V _{CE} = 5V, I _C = 50mA, f=50MHz
Turn-On Time	t _{on}	_	80	_	ns	$V_{CC} = 50V, I_{C} = 100mA$
Turn-Off Time	t _{off}		2,900	_	ns	$I_{B1} = -I_{B2} = 10mA$

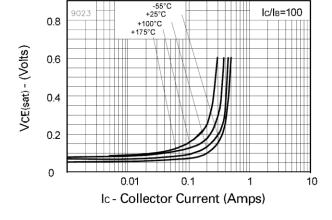
Note:

11. Measured under pulsed conditions. Pulse width ≤ 300 µs. Duty cycle ≤ 2%.



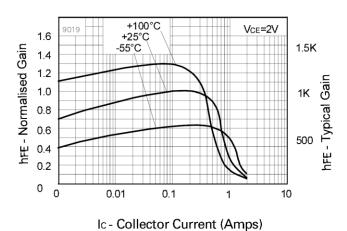
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

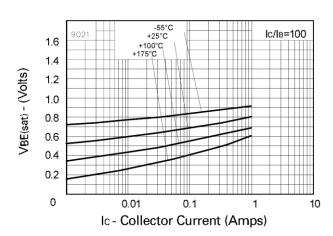




VCE(sat) v IC

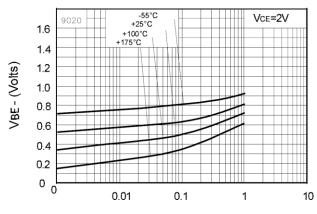
VCE(sat) v IC





hFE v IC

VBE(sat) v IC

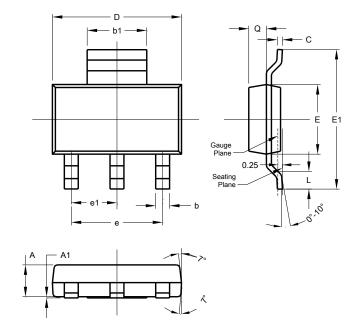


Ic - Collector Current (Amps) **VBE(on) v IC**



Package Outline Dimensions

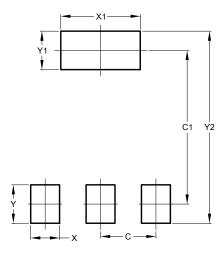
Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Υ	1.60		
Y1	1.60		
Y2	8.00		



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